

PWM Step-Up DC/DC Converter for Panel Backlight

General Description

The EMD2095 is a highly efficient, step-up DC/DC converter for driving white LEDs. The device can drive up to 9 serially connected white LEDs from a single Li-Ion battery, or to drive multiple serial and parallel combinations with a DC power supply from 2.5V to 5.5V. The EMD2095 uses current mode and pulse-width modulated (PWM) operation. Its high switching operation frequency of 1.2MHz allows the system to use small inductor, input and output capacitors. An internal compensation circuit can reduce the external component count.

To safeguard the system, the EMD2095 includes various protection circuits such as under-voltage lockout, current limit, over voltage and thermal shutdown. EMD2095 are available in the tiny packages of SOT-23-6L.

Applications

- Mobile Phone
- Digital Still Cameras
- Portable applications
- MP3 Players
- GPS Receivers

Features

- Up to 9 WLEDs supports
- Low Quiescent Current: 120 μ A
- Over Voltage Protection: 31V
- Inherently Matched LED Current
- Shutdown Current < 1 μ A
- Reference Voltage 0.245V
- PWM Dimming Control (2KHz~200kHz)
- Internal Soft Start and Compensation
- 1.4A Internal power MOSFET Switch
- Low Profile SOT-23-6 Package

Typical Application (9S3P)

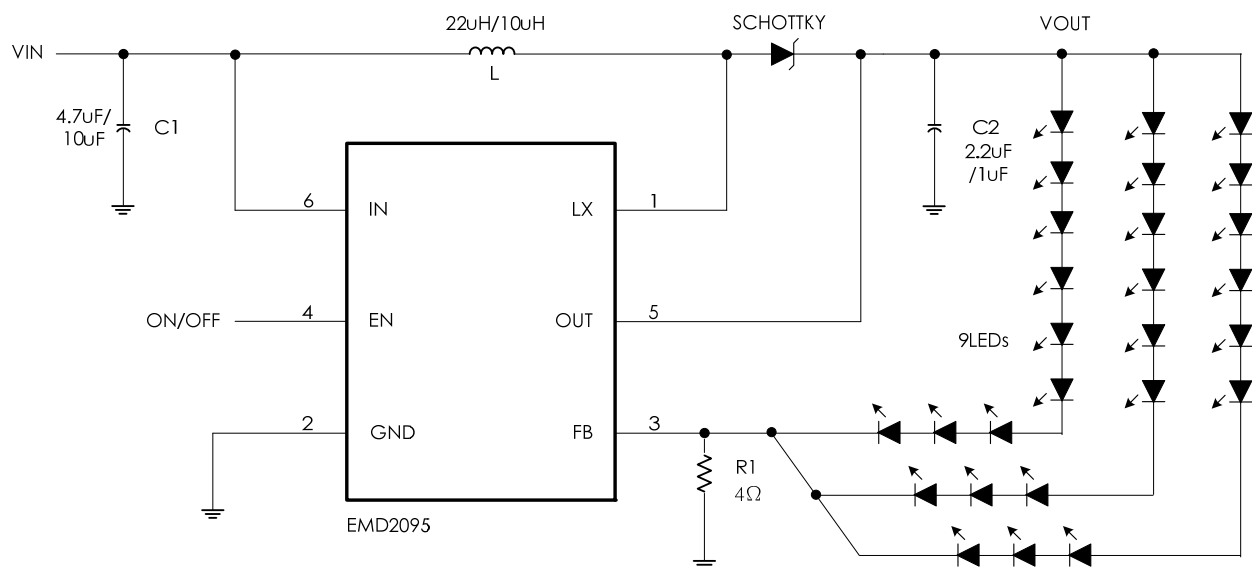
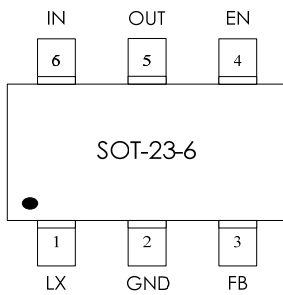


Fig. 1

Connection Diagram



Order Information

EMD2095-00VC06NRR
 00 Output voltage
 VC06 SOT-23-6L Package
 NRR RoHS & Halogen free package
 Rating: -40 to 85°C
 Package in Tape & Reel

Order, Marking & Packing Information

Package	Vout	Product ID	Marking	Packing
SOT-23-6L	Adjustable	EMD2095-00VC06NRR		Tape & Reel 3Kpcs

Function Block

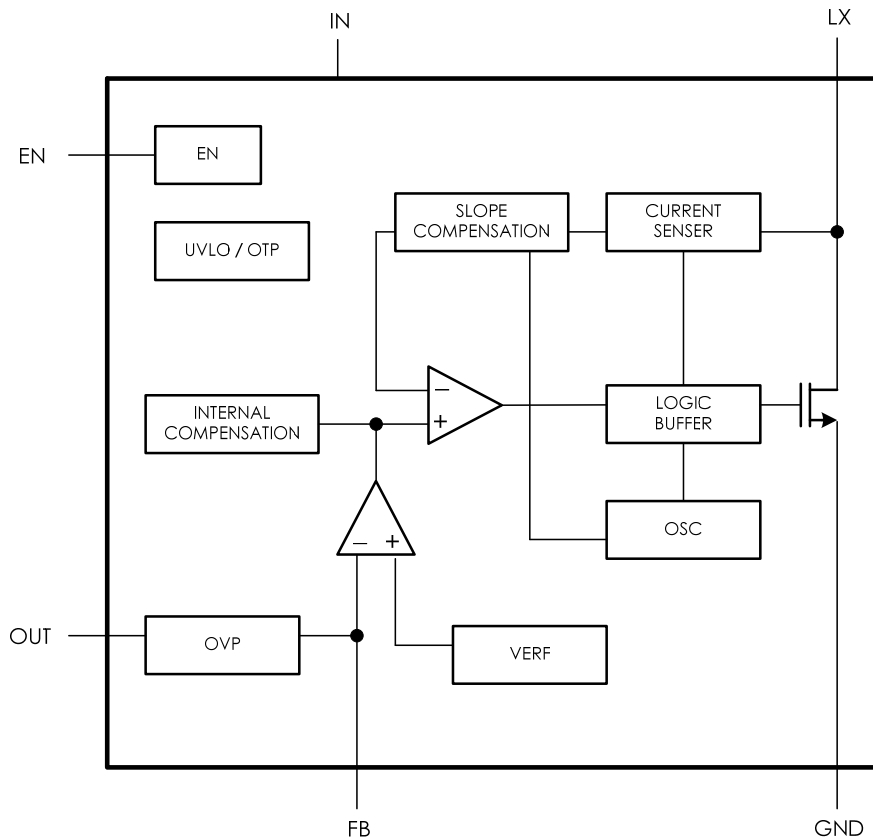


Fig. 2

Pin Functions

Pin Name	SOT-23-6L Pin #	Function
LX	1	Switch Pin. Connect inductor/diode here.
GND	2	Ground Pin.
FB	3	Feedback Pin. Reference voltage is 0.245V, connect cathode of lowest LED and resistor here.
EN	4	Chip Enable Pin and PWM Dimming Control Pin. Connect to 1.2V or higher to enable device, 0.4V or less to disable device.
OUT	5	Over Voltage Protection Pin.
IN	6	Input Voltage Pin.

Absolute Maximum Ratings

Devices are subjected to failure if they stay above absolute maximum ratings

Input Voltage	- 0.3V to 6V	Operating Temperature Range	-40°C to 85°C
EN, VFB Voltages	- 0.3V to VIN	Storage Temperature	-65°C to 150°C
LX ,OUT Voltage	-0.3V to 37V	Junction Temperature	150°C
ESD Susceptibility	HBM 2kV MM 200V	Lead Temperature (Soldering, 10 sec)	260°C

Thermal data

Package	Thermal resistance	Parameter	Value
SOT-23-5	θ_{JA} (Note 2)	Junction-ambient	250°C/W
	θ_{JC} (Note 3)	Junction-case	81°C/W

Note 1: T_J is a function of the ambient temperature T_A and power dissipation P_D ($T_J = T_A + (P_D) * (165^\circ\text{C}/\text{W})$).

Note 2: θ_{JA} is measured in the natural convection at $T_A=25^\circ\text{C}$ on a highly effective thermal conductivity test board (2 layers , 2SOP) according to the JEDEC 51-7 thermal measurement standard.

Note 3: θ_{JC} represents the heat resistance between the chip and the package top case.

Electrical Characteristics

$V_{IN} = 3.7\text{V}$, $C_{IN}=4.7\mu\text{F}$, $C_{OUT}=1\mu\text{F}$, $I_{OUT}=20\text{mA}$, $L=22\mu\text{H}$, $T_A = 25^\circ\text{C}$, unless otherwise specified.

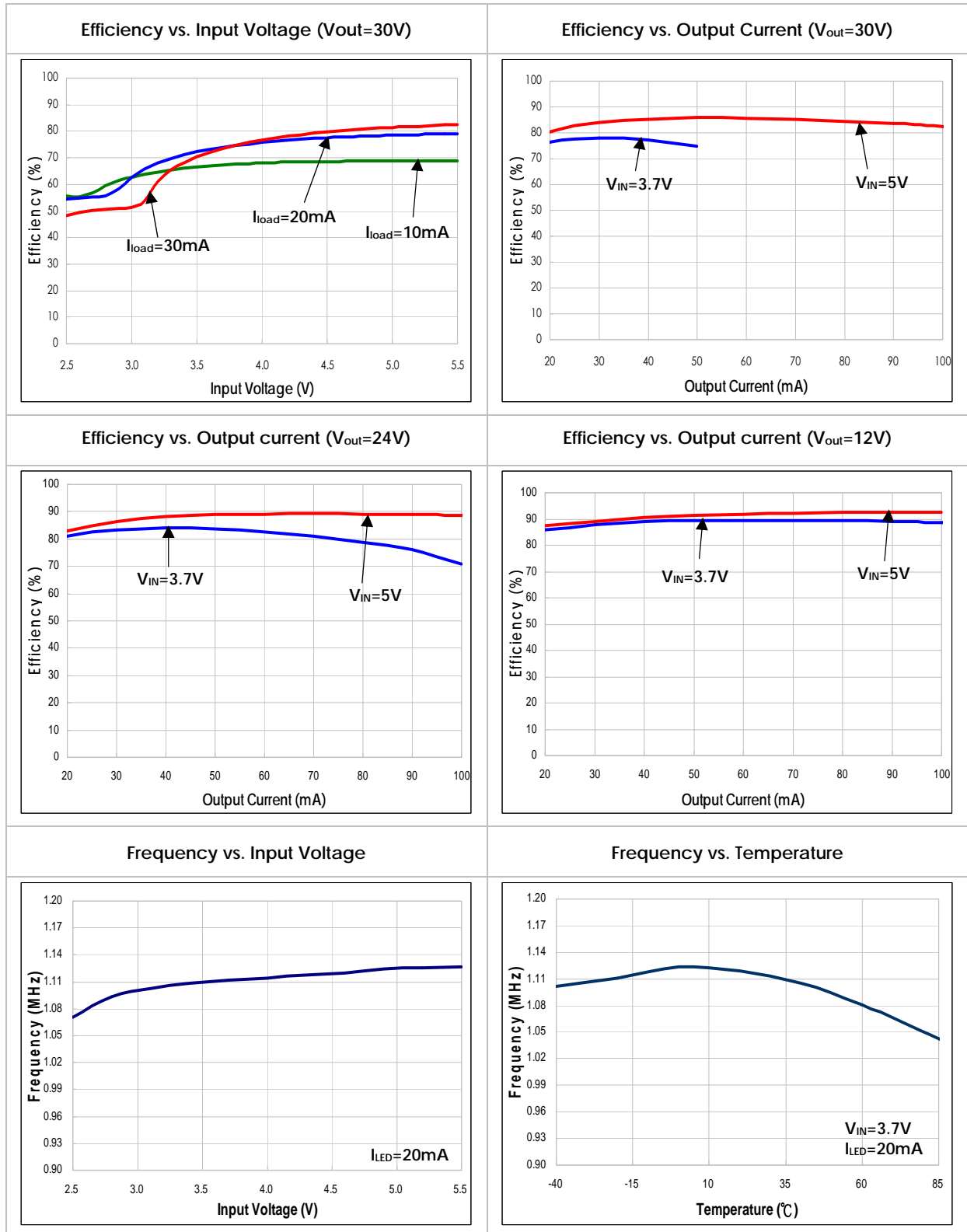
PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
Input Voltage		2.5		5.5	
Under Voltage Lock Out		1.8		2.4	V
UVLO Hysteresis			0.1		V
Supply Current	Continuously Switching			1	mA
Quiescent Current	No Switching		120		μA
Shutdown Current	$V_{EN} < 0.4\text{V}$			1	μA
Operation Frequency		0.9	1.2	1.5	MHz
Maximum Duty Cycle		93	95		%
Feedback Voltage		232.7	245	257.3	mV
Thermal Shutdown Protection			150		$^\circ\text{C}$
Thermal Shutdown Hysteresis			10		$^\circ\text{C}$
Ron	$I_{sw} = 200\text{mA}$		0.5	0.8	ohm
Current Limit			1.4		A
Shutdown Voltage Low		0.4			V
Enable Voltage High				1.2	V
EN Leakage Current			1.0		μA

Electrical Characteristics**V_{IN} = 3.7V, C_{IN}=4.7uF, C_{OUT}=1uF, I_{OUT}=20mA, L=22uH, T_A = 25°C, unless otherwise specified.**

PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
Maximum Output Voltage				30	V
OVP		31			V
OVP Hysteresis			1	3	V

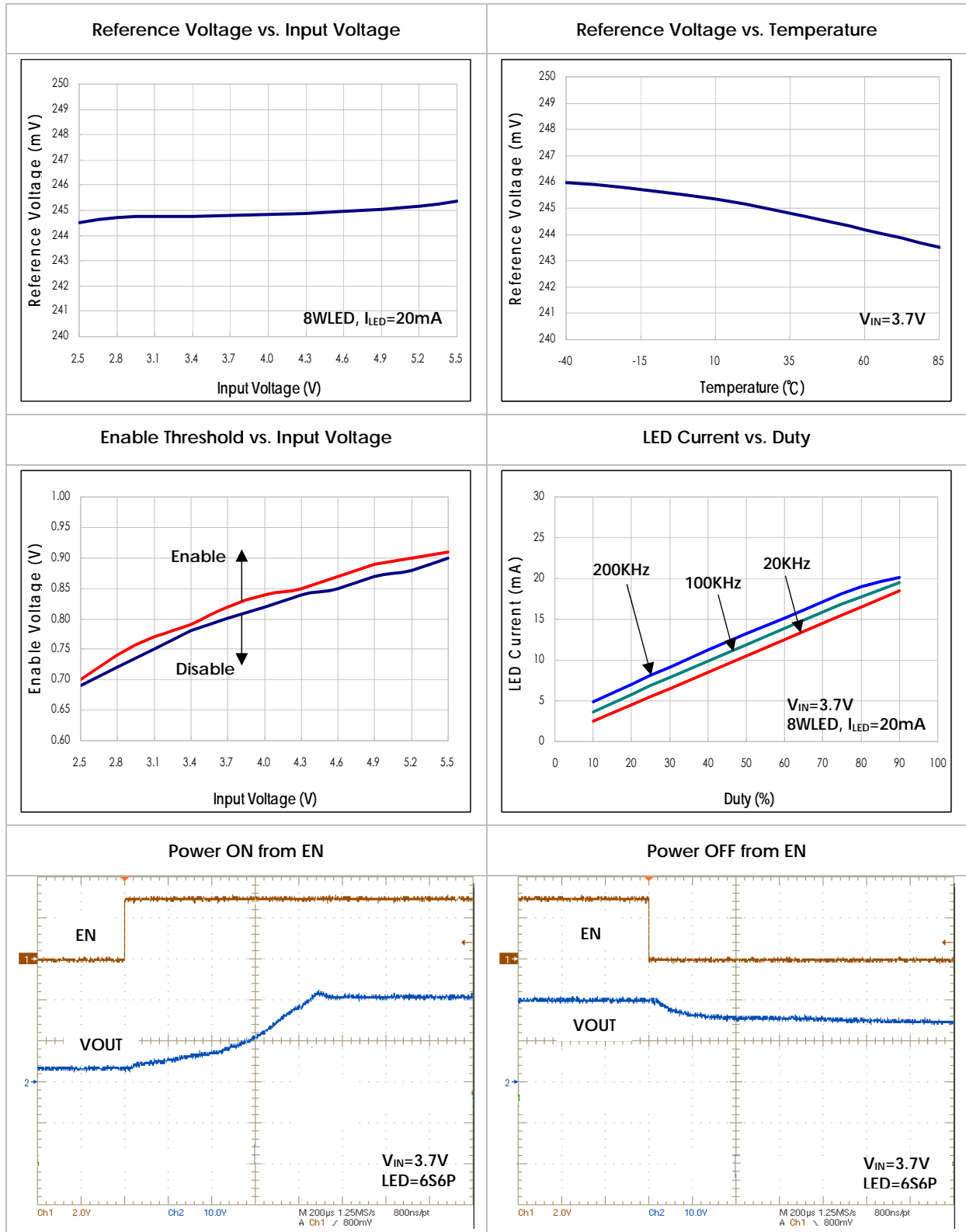
Typical Performance Characteristics

$V_{IN} = 3.7V$, $C_{IN} = 4.7\mu F$, $C_{OUT} = 1\mu F$, $I_{OUT} = 20mA$, $L = 22\mu H$, $T_A = 25^\circ C$, unless otherwise specified.



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Application Information

Detailed Description

The EMD2095 is a constant frequency current-mode boost converter, which can driver 9 series of WLED. The device provides the same output current through each WLED that get even illumination. The fast operation frequency allows for small inductor and input/output capacitors.

During normal operation, the internal oscillators send a pulse signal to set latch and turn on internal MOSFET each duty circle. A current sense voltage sums MOSFET current and slope signal connected to the negative terminal of the PWM comparator. When this signal voltage exceeds output voltage of error amplifier, the PWM comparator will send a signal to reset latch and turn off internal MOSFET. The output voltage of error amplifier is magnified from the difference between reference voltage and feedback voltage. If reference voltage is higher than feedback voltage, more current is delivered to the output, the other way, less current is delivered.

UVLO

The EMD2095 provides under voltage lock out protection. When VIN is down close to UVLO threshold, the UVLO block will send a signal to turn off power MOSFET. The device stops to supply current to output. The 100mV hysteresis prevents supply transients from causing a restart. Once the VIN exceed UVLO threshold, the device unlocks latch and turn power MOSFET.

Enable / Disable

The EMD2095 enter shutdown mode when EN pin voltage is less 0.4V. When in shutdown mode, all internal circuits of the EMD2095 are turn off and quiescent current is reduced to 1uA. When driver EN pin voltage is higher than 1.2V, start-up begins.

EN pin can be used for dimming control, the PWM frequency range is from 2KHz to 200kHz. The average LED current is proportional to the PWM duty cycle, while 0% duty cycle triggers zero WLEDs current and 100% duty cycle triggers full WLEDs current.

OVP

When WLEDs are open, the boost control loop just like open loop operation, it may causes over voltage damage on LX pin. In order to prevent this damage, the EMD2095 provides OVP function to provide it. The protection threshold is set at 31V.

OTP

The internal thermal sensor turn off power MOSFET when junction temperature is exceeded 150°C, the OTP is designed with a 10°C hysteresis.

LED Current Setting

Referring to Figure 1 of the typical application, adjusting the output current changes the brightness of WLEDs, the EMD2095 regulates output current by sense resistor (R1). The output current is given by:

$$\text{LED current} = 0.245\text{V} / R1$$

C_{in} and C_{out} Selection

It is recommended to use the X5R or X7R which have best temperature and voltage characteristics of all the ceramics for a give value and size. A minimum input capacitance of 1μF is required for the EMD2095, the capacitor value may be increased without limit, and higher capacitance can stable the switching voltage (LX) at low temperature. The typical output capacitor value is 1μF, higher capacitance can be used to reduce voltage ripple.

Inductor Selection

The inductor values range from 4.7μH to 22μH. The typical inductor value is 22μH. The low DCR inductor is preferred. In addition, the limit saturation current of inductor must exceed current limit of the EMD2095.

Diode Selection

Referring to Figure 1 of the typical application, the EMD2095 is high switching control devise which demands a high speed rectification diode for optimum efficiency. The schottky diode is preferred, for high efficiency, schottky diode provide fast recovery time and low forward voltage that reduce power loss. The recover breakdown voltage of schottky diode must exceed output voltage.

Application Circuit

- Application circuit for 9S1P

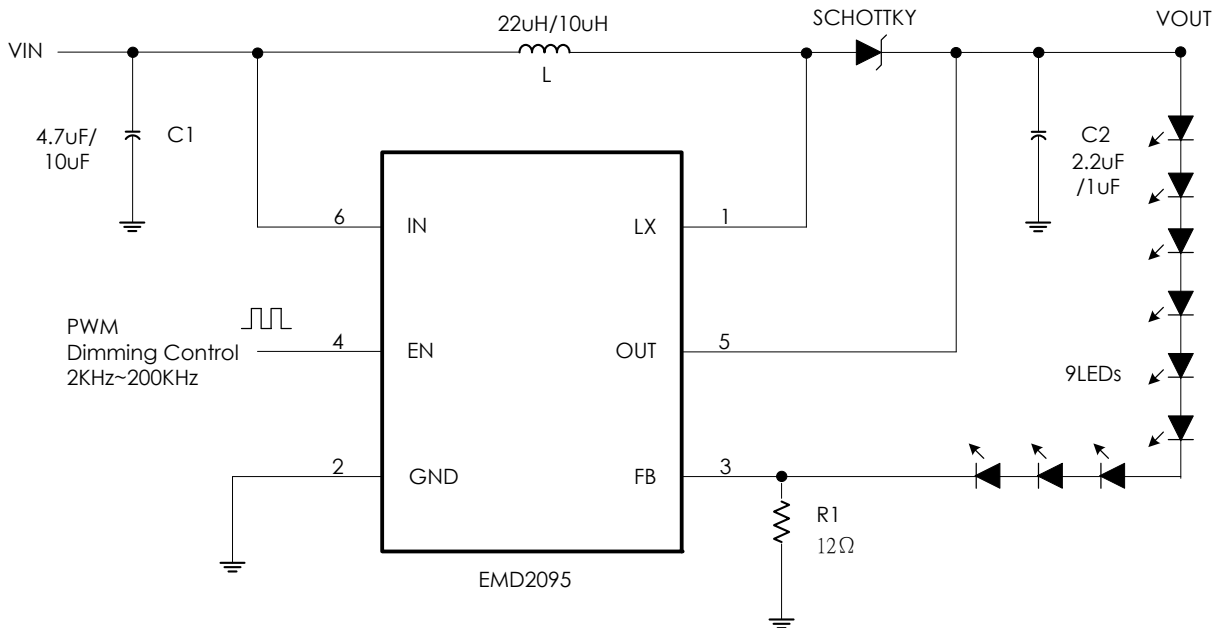


Fig. 3

- Application circuit for 9S3P

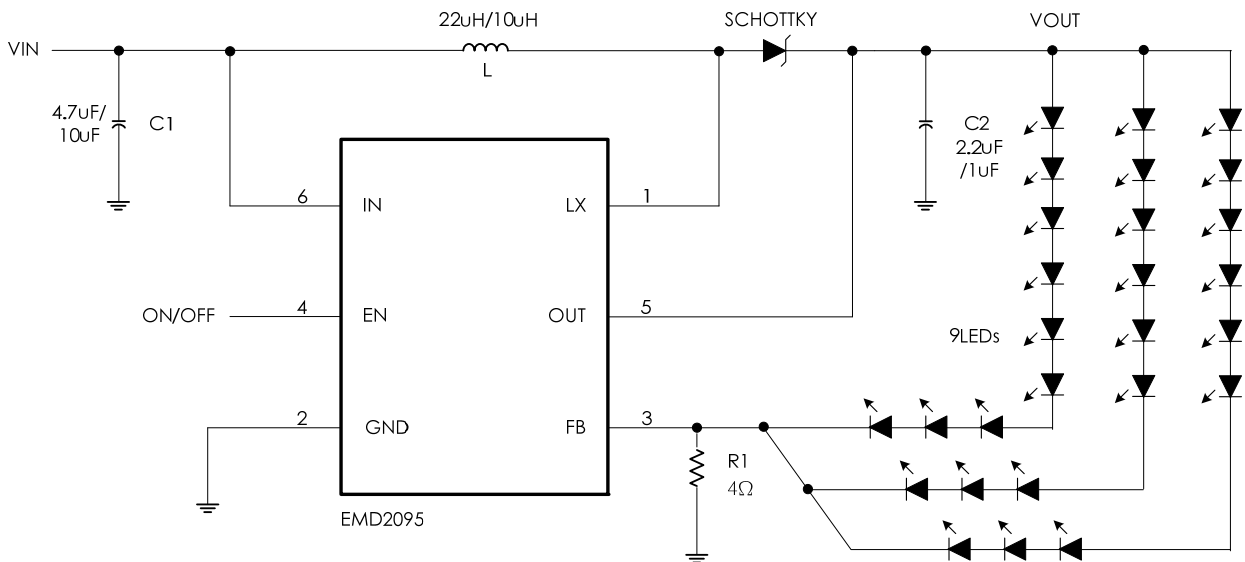
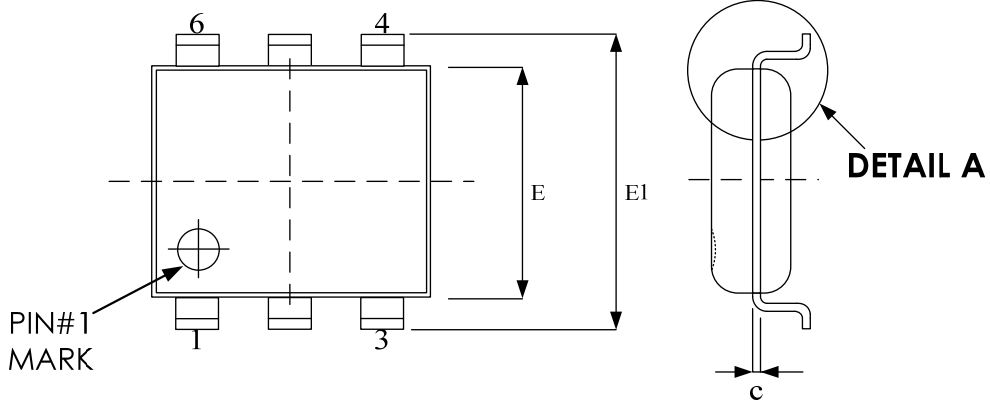
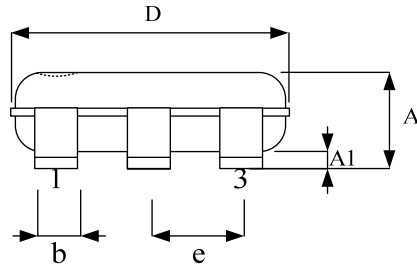


Fig. 4

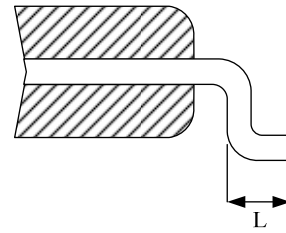
Package Outline Drawing
SOT-23-6



TOP VIEW



SIDE VIEW



DETAIL A

Symbol	Dimension in mm	
	Min.	Max.
A	0.90	1.45
A1	0.00	0.15
b	0.30	0.50
c	0.08	0.25
D	2.70	3.10
E	1.40	1.80
E1	2.60	3.00
e	0.95 BSC	
L	0.30	0.60

Revision History

Revision	Date	Description
0.1	2013.10.09	Initial version.
0.2	2013.11.20	Revise VFB spec to 5% from 3%

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